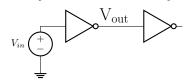
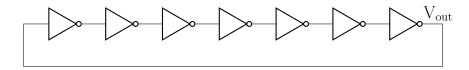
EC 5311 Digital IC Design: Assignment 5 Ring oscillator – post-layout extracted simulation

$$V_{Tn} = 0.7, \quad \mu_n = 0.025 \,\mathrm{m}^2/\mathrm{V} - \mathrm{s}, \quad C_{oxn} = 8.34 \,\mathrm{fF}/\mathrm{\mu m}^2, \quad vsat_n = 8 \times 10^4 \mathrm{m/s}, \quad \lambda_n = 0.2 \\ |V_{Tp}| = 0.7, \quad \mu_p = 0.009 \,\mathrm{m}^2/\mathrm{V} - \mathrm{s}, \quad C_{oxp} = 8.16 \,\mathrm{fF}/\mathrm{\mu m}^2, \quad vsat_p = 3 \times 10^4 \,\mathrm{m/s}, \quad \lambda_p = 0.2.$$

- 1. Draw a DRC and LVS clean layout of the CMOS inverter with the minimum delay from Assignment 3.
 - (a) Extract the parasitic values from the layout and find the delay of the inverter using the circuit:



- (b) Measure the delay including the layout parasitic of net V_{out}.
- 2. Using the inverter layout above, draw the layout of a seven stage ring oscillator shown below.



To ensure oscillation in the transient simulation, set the node $V_{out} = 0$ V initially using: .ic v(Vout)=0

- (a) Measure the oscillating frequency for $V_{DD} = 1.8 \text{V}$ with the layout parasitics.
- (b) Plot the oscillating frequency and time period as a function of V_{DD} for $V_{DD} = 1$ V to 1.8V in steps of 0.1V.
- (c) Compare the frequencies against pre-layout simulation in Assignment 4.